MOS FIELD EFFECT POWER TRANSISTORS

2SK739, 2SK739-Z

FAST SWITCHING
N-CHANNEL SILICON POWER MOS FET
INDUSTRIAL USE

FEATURES

- Suitable for switching power supplies, actuater controls, and pulse circuits.
- Low $R_{DS(on)}$
- No second breakdown
- 4 V Gate Drive – Logic level –
- Designed for Hybrid Integrated Circuits

ABSOLUTE MAXIMUM RATINGS (T_a = 25 °C)

Drain to Source Voltage	V_{DSS}	60	V
Gate to Source Voltage	V_{GSS}	±20	V
Continuous Drain Current	$I_{D(DC)}$	±2.0	A
Peak Drain Current	$I_{D(pulse)}$*	±8.0	A
Total Power Dissipation	P_T**	20	W
Total Power Dissipation at 25 °C Ambient Temperature	P_T***	2.0	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	−55 to +150	°C

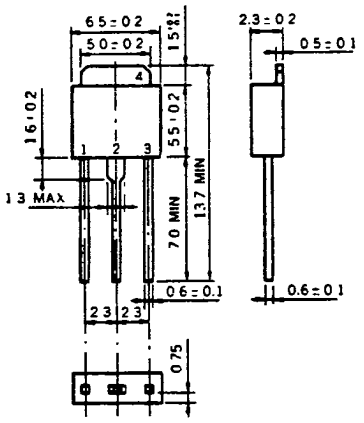
* PW ≤ 300 μs, Duty Cycle ≤ 10 %
** T_C = 25 °C
*** Mounted on ceramic substrate of 2.5 cm² x 0.7 mm

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

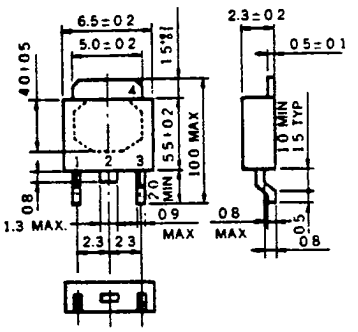
CHARACTERISTIC	SYMBOL	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
Drain Leakage Current	I_{DSS}			10	μA	V_{DS} = 60 V, V_{GS} = 0
Gate to Source Leakage Current	I_{GSS}			±100	nA	V_{GS} = ±20 V, V_{DS} = 0
Gate to Source Cutoff Voltage	$V_{GS(off)}$	1.0		2.5	V	V_{DS} = 10 V, I_D = 1 mA
Forward Transfer Admittance	$\|Y_{fs}\|$	1.0			S	V_{DS} = 10 V, I_D = 1 A
Drain to Source On-State Resistance	$R_{DS(on)}$		0.17	0.25	Ω	V_{GS} = 10 V, I_D = 1 A
Drain to Source On-State Resistance	$R_{DS(on)}$		0.22	0.35	Ω	V_{GS} = 4 V, I_D = 0.8 A
Input Capacitance	C_{iss}		550		pF	V_{DS} = 10 V, V_{GS} = 0 f = 1 MHz
Output Capacitance	C_{oss}		200		pF	
Reverse Transfer Capacitance	C_{rss}		60		pF	
Turn-On Delay Time	$t_{d(on)}$		10		ns	I_D = 1 A, V_{CC} = 30 V $V_{GS(on)}$ = 10 V R_L = 30 Ω R_{in} = 10 Ω
Rise Time	t_r		20		ns	
Turn-Off Delay Time	$t_{d(off)}$		80		ns	
Fall Time	t_f		20		ns	

PACKAGE DIMENSIONS (Unit: mm)

2SK739



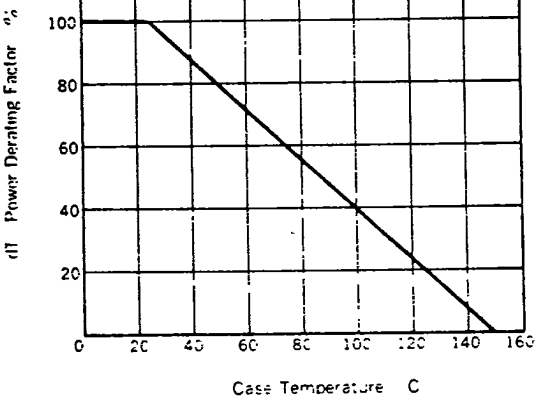
2SK739-Z



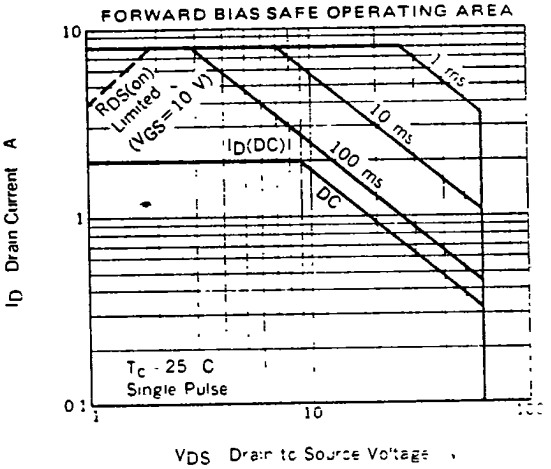
1. Gate
2. Drain
3. Source
4. Drain (Fin)

TYPICAL CHARACTERISTICS (T_a = 25 °C)

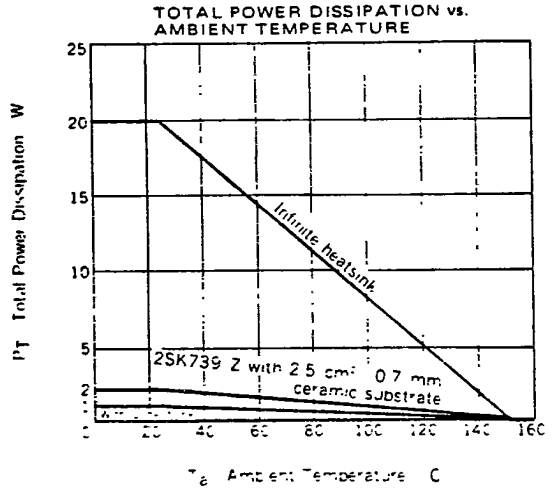
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



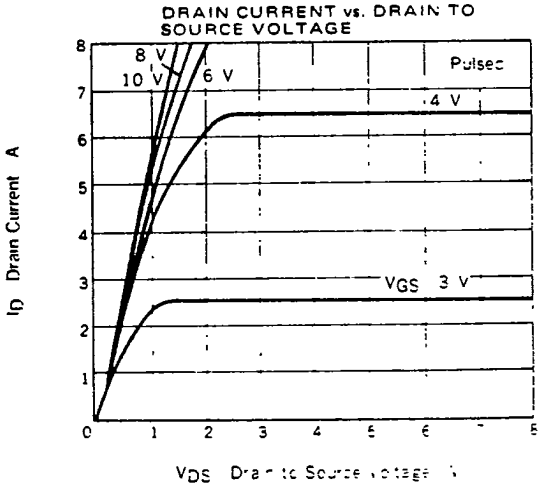
FORWARD BIAS SAFE OPERATING AREA



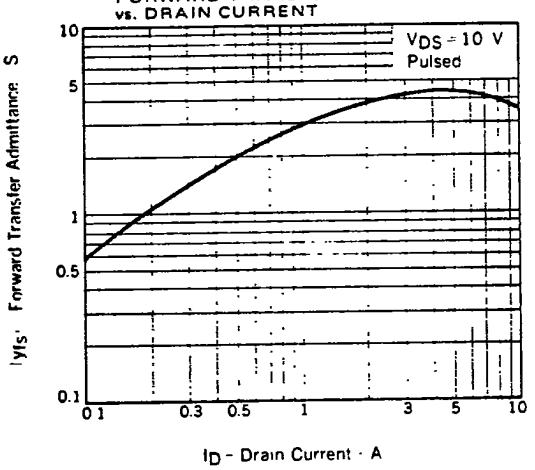
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



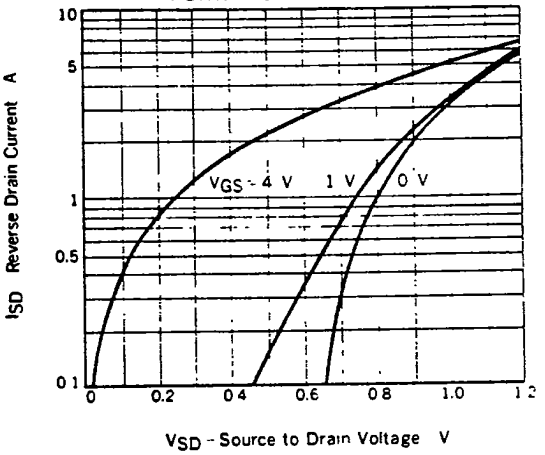
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



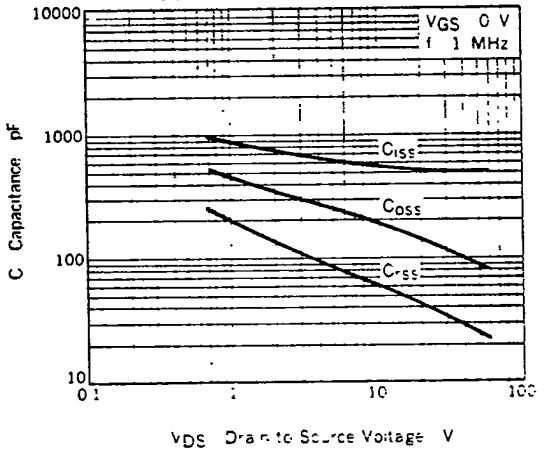
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



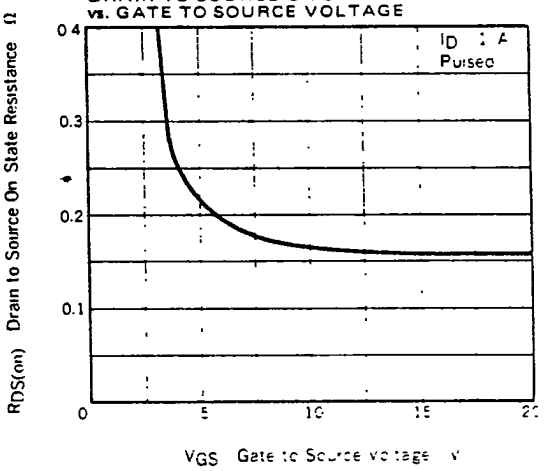
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



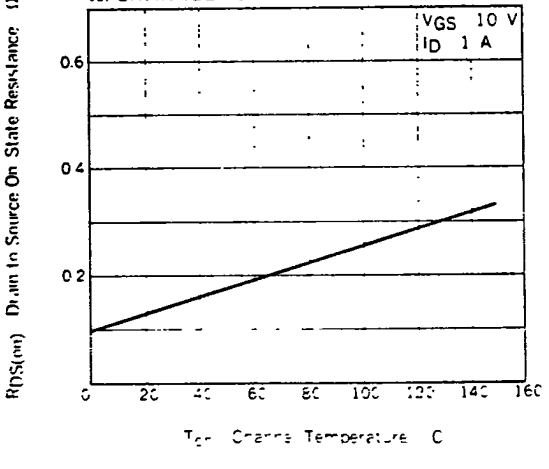
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



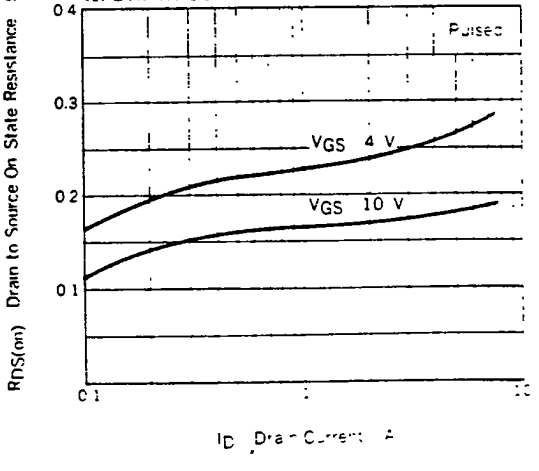
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



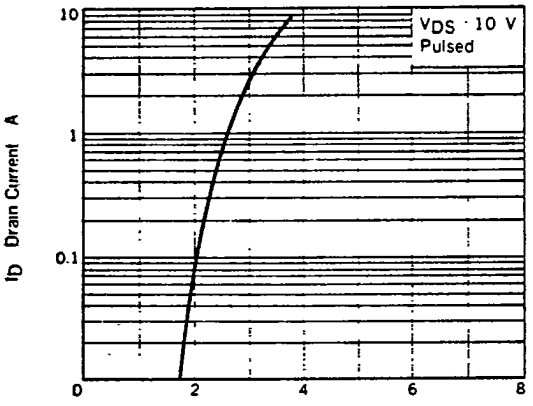
DRAIN TO SOURCE ON STATE RESISTANCE vs. CHANNEL TEMPERATURE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

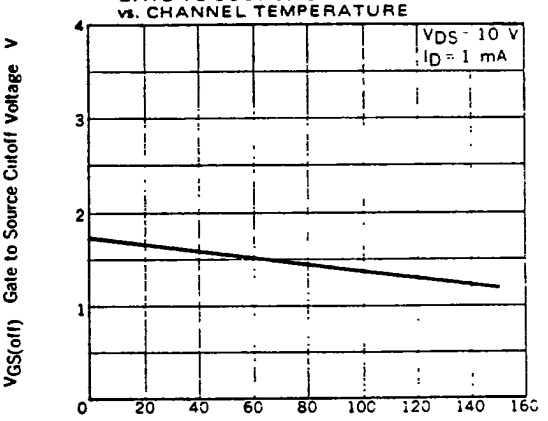


TYPICAL TRANSFER CHARACTERISTICS



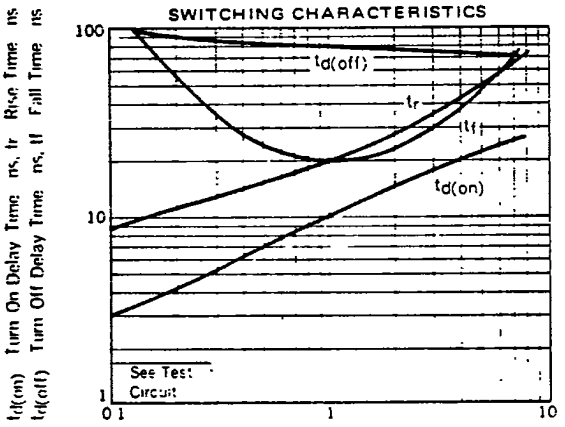
VGS Gate to Source Voltage V

GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



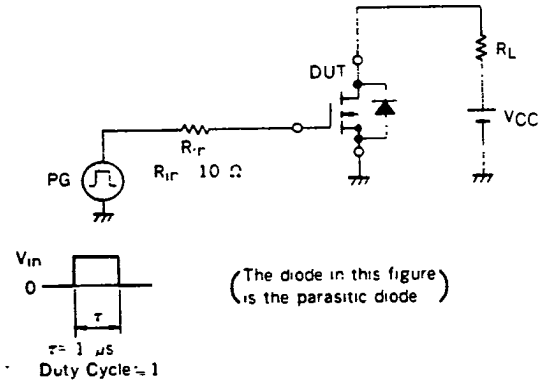
Tch – Channel Temperature C

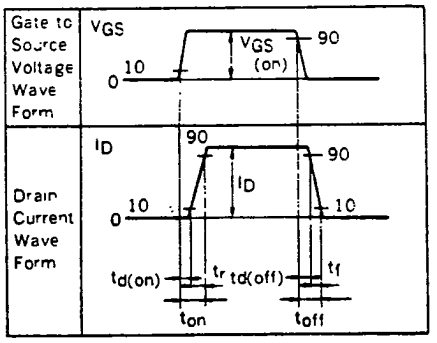
SWITCHING CHARACTERISTICS



ID Drain Current A

SWITCHING TIME TEST CIRCUIT





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